

IN THE CLAIMS:

Please amend the claims as follows:

- 1-22. (Canceled)
23. (Currently Amended) A pixel, comprising:
a single-layered substrate further comprising:
a generally planar surface comprising semiconductive material, and
at least one protuberance from said generally planar surface; and
an impurity offset from said generally planar surface and within said protuberance,
wherein said impurity within said protuberance has a concentration increasing
concurrently with a distance from said generally planar surface.
24. (Previously Presented) The pixel in claim 23, wherein said impurity is located
within said protuberance to the exclusion of said substrate.
25. (Previously Presented) A field emission display, comprising:
an uncontaminated single-layered substrate that is at least semiconductive; and
a micro-cathode on said substrate, further comprising:
a contaminated apex, and
a decreasingly contaminated body.
26. (Previously Presented) The field emission display of claim 25, wherein said
micro-cathode is integral with said substrate.
27. (Currently Amended) A display panel, comprising:
a generally uncontaminated substrate comprising semiconductive material; and
an emitter electrode on said substrate, further comprising an apex, and further having an etch-
resistible quality that increases with depth from said apex.

28. (Previously Presented) The display panel in claim 27, wherein said emitter electrode further comprises a base and further has an oxidizable quality that increases with elevation from said base.

29. (Previously Presented) The display panel in claim 28, wherein a portion of said substrate that is under said emitter electrode has an etch-resistible quality generally similar to an etch-resistible quality of said base.

30. (Previously Presented) The display panel in claim 29, wherein said portion has an oxidizable quality generally similar to an oxidizable quality of said base.

31. (Currently Amended) A cathode conductor system, comprising:
a tip further comprising:
 an apex, and
 a base under said apex;
a substrate comprising semiconductive material, indivisibly extending from said base; and
a dopant in said tip defining a concentration gradient from said apex to said base and further defining a uniform concentration under said base.

32. (Previously Presented) The cathode conductor system in claim 31, wherein said dopant defines a concentration of generally zero within said substrate.